TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

32,768-WORD BY 8-BIT STATIC RAM

DESCRIPTION

The TC55257DPL/DFL/DFTL/DTRL is a 262,144-bit static random access memory (SRAM) organized as 32,768 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 5 V ± 10% power supply. Advanced circuit technology provides both high speed and low power at an operating current of 5 mA/MHz (typ) and a minimum cycle time of 55 ns. It is automatically placed in low-power mode at 0.3 μA standby current (typ) when chip enable ($\overline{CE}$) is asserted high. There are two control inputs. $\overline{CE}$ is used to select the device and for data retention control, and output enable ($\overline{OE}$) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. The TC55257DPL/DFL/DFTL/DTRL is available in a standard plastic 28-pin dual-in-line package (DIP), plastic 28-pin small-outline package (SOP) and normal and reverse pinout plastic 28-pin thin-small-outline package (TSOP).

FEATURES

- Low-power dissipation
  Operating: 27.5 mW/MHz (typical)
- Standby current of 2 μA (maximum) at Ta = 25°C
- Single power supply voltage of 5 V ± 10%
- Power down features using $\overline{CE}$.
- Data retention supply voltage of 2 to 5.5 V
- Direct TTL compatibility for all inputs and outputs

- Access Times (maximum):

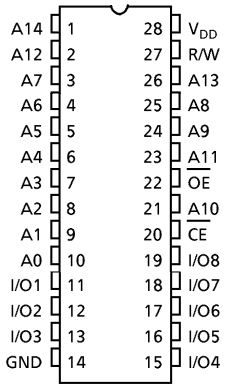
	TC55257DPL/DFL/DFTL/DTRL		
	-55L	-70L	-85L
Access Time	55 ns	70 ns	85 ns
$\overline{CE}$ Access Time	55 ns	70 ns	85 ns
$\overline{OE}$ Access Time	30 ns	35 ns	45 ns

Packages:

DIP28-P-600-2.54 (DPL)	(Weight: 4.42 g typ)
SOP28-P-450-1.27 (DFL)	(Weight: 0.79 g typ)
TSOP I 28-P-0.55 (DFTL)	(Weight: 0.22 g typ)
TSOP I 28-P-0.55A (DTRL)	(Weight: 0.22 g typ)

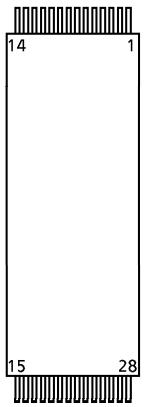
PIN ASSIGNMENT (TOP VIEW)

○ 28 PIN DIP & SOP

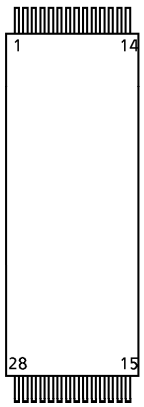


○ 28 PIN TSOP

(Normal pinout)



(Reverse pinout)



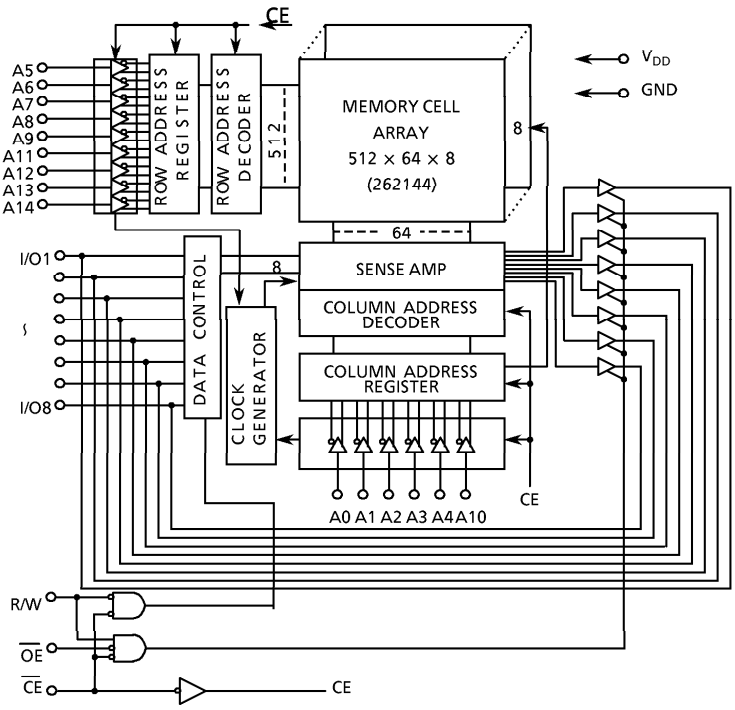
PIN NAMES

A0 to A14	Address Inputs
R/W	Read/Write Control
$\overline{OE}$	Output Enable
$\overline{CE}$	Chip Enable
I/O1 to I/O8	Data Input/Output
V_{DD}	Power (+ 5 V)
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PIN NAME	$\overline{OE}$	A_{11}	A_9	A_8	A_{13}	R/W	V_{DD}	A_{14}	A_{12}	A_7	A_6	A_5	A_4	A_3
PIN NO.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
PIN NAME	A_2	A_1	A_0	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	$\overline{CE}$	A_{10}

961001EBA1

BLOCK DIAGRAM



OPERATION MODE

MODE	$\overline{CE}$	$\overline{OE}$	R/W	I/O1 to I/O8	POWER
Read	L	L	H	D_{OUT}	I_{DDO}
Write	L	×	L	D_{IN}	I_{DDO}
Outputs Disabled	L	H	H	High-Z	I_{DDO}
Standby	H	×	×	High-Z	I_{DDS}

Note: × = don't care. H = logic high. L = logic low.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V_{DD}	Power Supply Voltage	− 0.3 to 7.0	V
V_{IN}	Input Voltage	− 0.3* to 7.0	V
$V_{I/O}$	Input/Output Voltage	− 0.5* to V_{DD} + 0.5	V
P_D	Power Dissipation	1.0/0.6 **	W
Tsolder	Soldering Temperature (10 s)	260	°C
Tstrg	Storage Temperature	− 55 to 150	°C
Topr	Operating Temperature	0 to 70	°C

* − 3.0 V when measured at a pulse width of 50 ns
** SOP

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V_{IH}	Input High Voltage	2.2	–	V_{DD} + 0.3	
V_{IL}	Input Low Voltage	– 0.3*	–	0.8	
V_{DH}	Data Retention Supply Voltage	2.0	–	5.5	

* – 3.0 V when measured at a pulse width of 50 ns

DC CHARACTERISTICS (Ta = 0° to 70°C, V_{DD} = 5 V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0 V to V_{DD}		–	–	± 1.0	μA
I_{OH}	Output High Current	V_{OH} = 2.4 V		– 1.0	–	–	mA
I_{OL}	Output Low Current	V_{OL} = 0.4 V		4.0	–	–	mA
I_{LO}	Output Leakage Current	$\overline{CE}$ = V_{IH} or R/W = V_{IL} or $\overline{OE}$ = V_{IH} V_{OUT} = 0 V to V_{DD}		–	–	± 1.0	μA
I_{DDO1}	Operating Current	$\overline{CE}$ = V_{IL} R/W = V_{IH}, I_{OUT} = 0 mA Other Inputs = V_{IH}/V_{IL}	t_{cycle} = 1 μs	–	10	–	mA
			t_{cycle} = min	–	–	70	
I_{DDO2}		$\overline{CE}$ = 0.2 V R/W = V_{DD} – 0.2 V, I_{OUT} = 0 mA Other Inputs = V_{DD} – 0.2 V/0.2 V	t_{cycle} = 1 μs	–	5	–	mA
			t_{cycle} = min	–	–	60	
I_{DDS1}	Standby Current	$\overline{CE}$ = V_{IH}		–	–	3	mA
I_{DDS2}		$\overline{CE}$ = V_{DD} – 0.2 V V_{DD} = 2.0 to 5.5 V	Ta = 0° to 70°C	–	–	20	μA
			Ta = 25°C	–	0.3	2	

CAPACITANCE (Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	V_{IN} = GND	10	pF
C_{OUT}	Output Capacitance	V_{OUT} = GND	10	pF

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS (Ta = 0° to 70°C, V_{DD} = 5 V ± 10%)

READ CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55L		-70L		-85L		
		MIN	MAX	MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	55	–	70	–	85	–	ns
t_{ACC}	Address Access Time	–	55	–	70	–	85	
t_{CO}	Chip Enable Access Time	–	55	–	70	–	85	
t_{OE}	Output Enable Access Time	–	30	–	35	–	45	
t_{COE}	Chip Enable Low to Output Active	10	–	10	–	10	–	
t_{OEE}	Output Enable Low to Output Active	5	–	5	–	5	–	
t_{OD}	Chip Enable High to Output High-Z	–	20	–	25	–	30	
t_{ODO}	Output Enable High to Output High-Z	–	20	–	25	–	30	
t_{OH}	Output Data Hold Time	10	–	10	–	10	–	

WRITE CYCLE

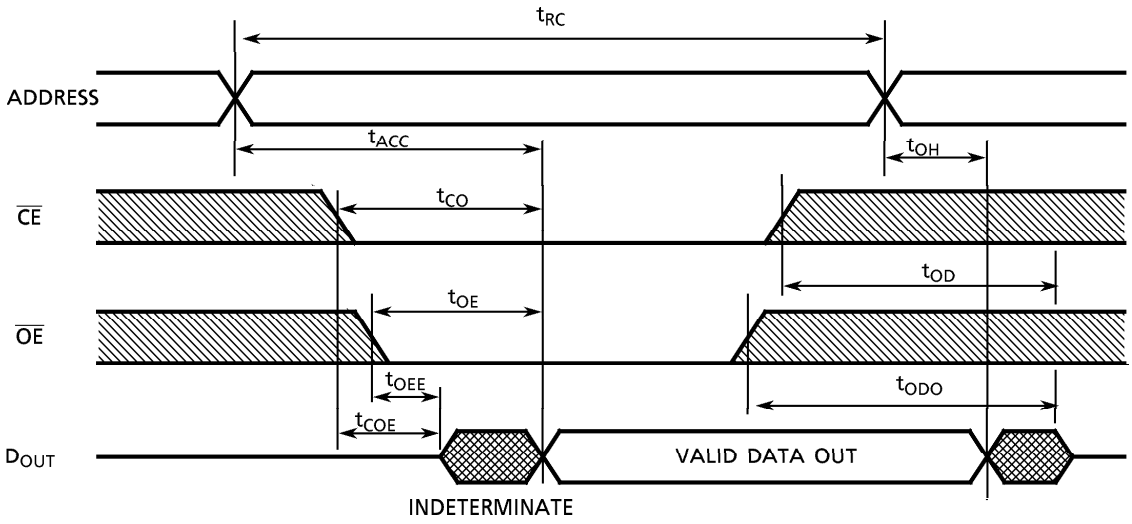
SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55L		-70L		-85L		
		MIN	MAX	MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	55	–	70	–	85	–	ns
t_{WP}	Write Pulse Width	45	–	50	–	60	–	
t_{CW}	Chip Enable to End of Write	50	–	60	–	65	–	
t_{AS}	Address Setup Time	0	–	0	–	0	–	
t_{WR}	Write Recovery Time	0	–	0	–	0	–	
t_{ODW}	R/W Low to Output High-Z	–	20	–	25	–	30	
t_{OEW}	R/W High to Output Active	5	–	5	–	5	–	
t_{DS}	Data Setup Time	25	–	30	–	40	–	
t_{DH}	Data Hold Time	0	–	0	–	0	–	

AC TEST CONDITIONS

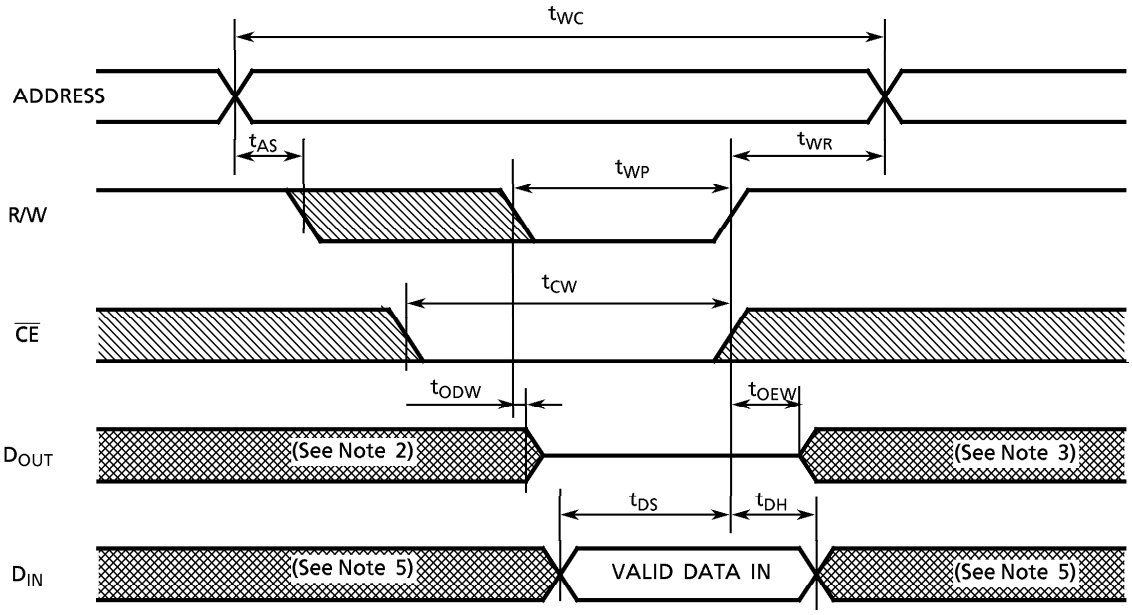
Output load: 30 pF + one TTL gate (-55L)
100 pF + one TTL gate (-70L, -85L)
Input pulse level: 0.6 V, 2.4 V
Timing measurements: 1.5 V
Reference level: 1.5 V
t_R, t_F: 5 ns

TIMING DIAGRAMS

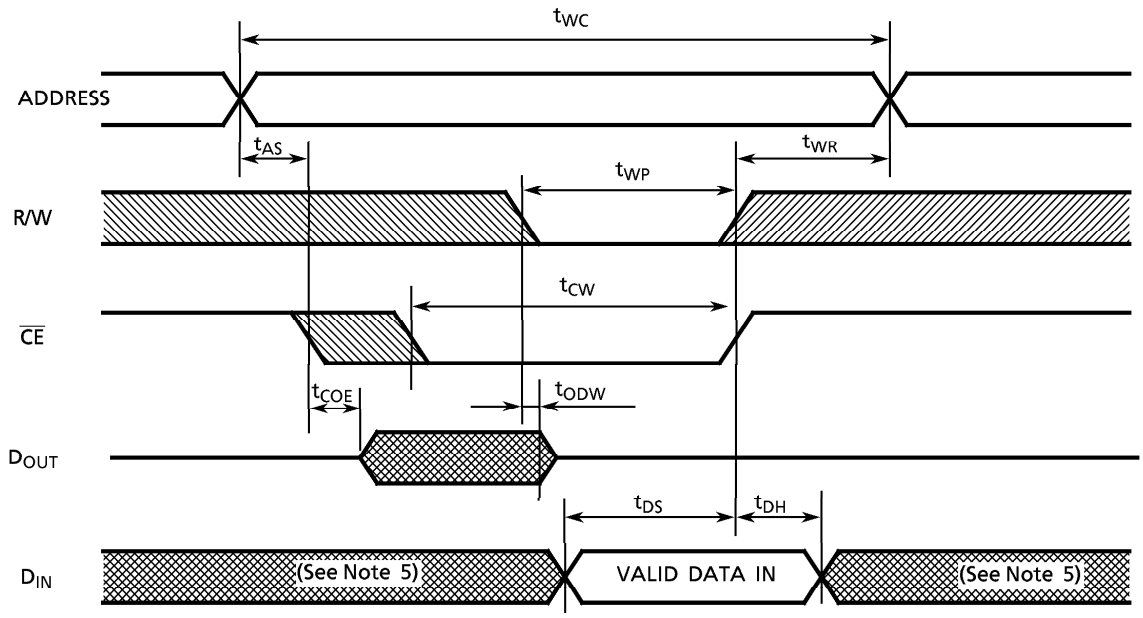
READ CYCLE (See Note 1)



WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



WRITE CYCLE 2 ($\overline{CE}$ CONTROLLED) (See Note 4)



Note: (1) R/W remains HIGH for the read cycle.

(2) If $\overline{CE}$ goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If $\overline{CE}$ goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

(4) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

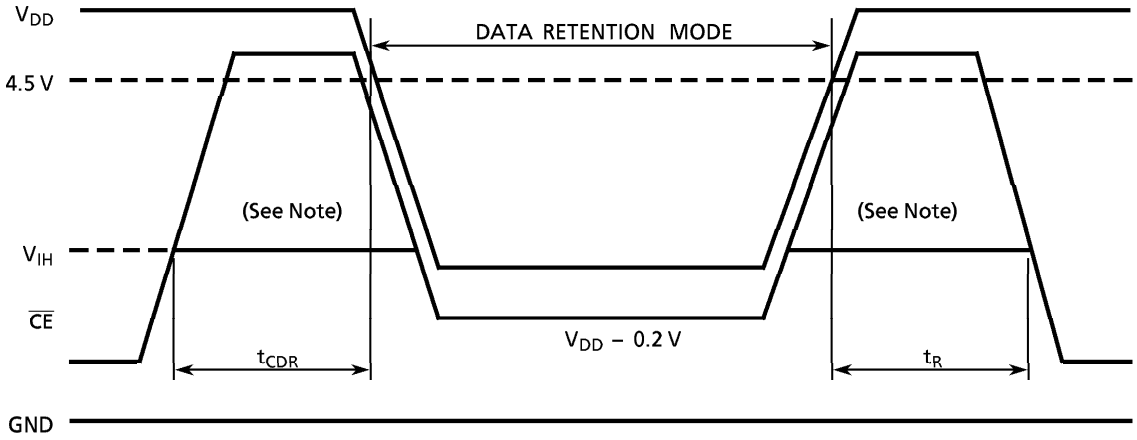
DATA RETENTION CHARACTERISTICS (Ta = 0° to 70°C)

SYMBOL	PARAMETER		MIN	TYP	MAX	UNIT
V_{DH}	Data Retention Supply Voltage		2.0	–	5.5	V
I_{DDS2}	Standby Current	V_{DH} = 3.0 V	–	–	10*	μA
		V_{DH} = 5.5 V	–	–	20	
t_{CDR}	Chip Deselect to Data Retention Mode Time		0	–	–	ns
t_R	Recovery Time		t_{RC} (See Note)	–	–	

* 2 μA (max) at Ta = 0° to 40°C

Note: Read cycle time.

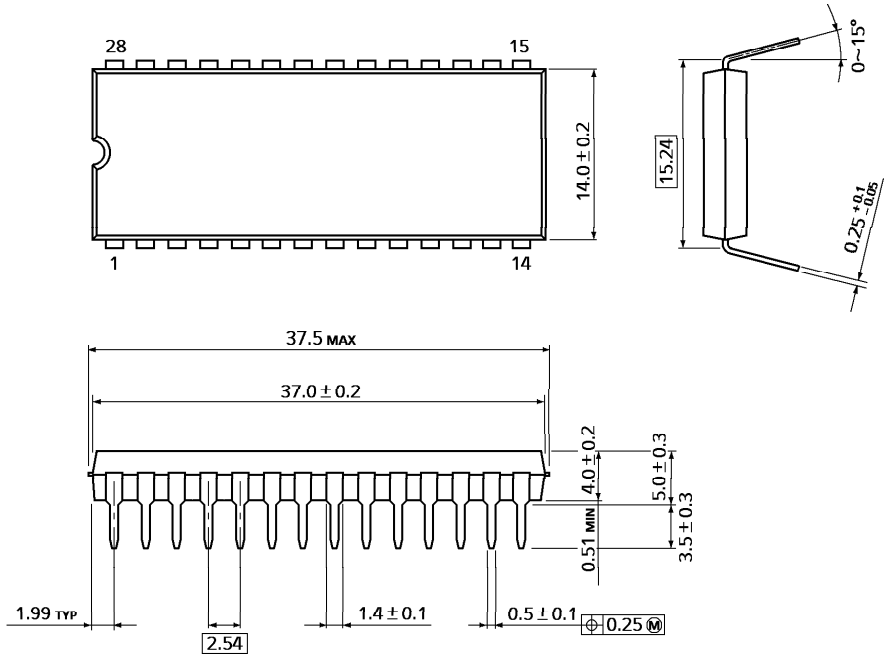
$\overline{CE}$ CONTROLLED DATA RETENTION MODE



Note: When $\overline{CE}$ is operating at the V_{IH} level (2.2 V), the standby current is given by I_{DDS1} during the transition of V_{DD} from 4.5 to 2.4 V.

PACKAGE DIMENSIONS (DIP28-P-600-2.54)

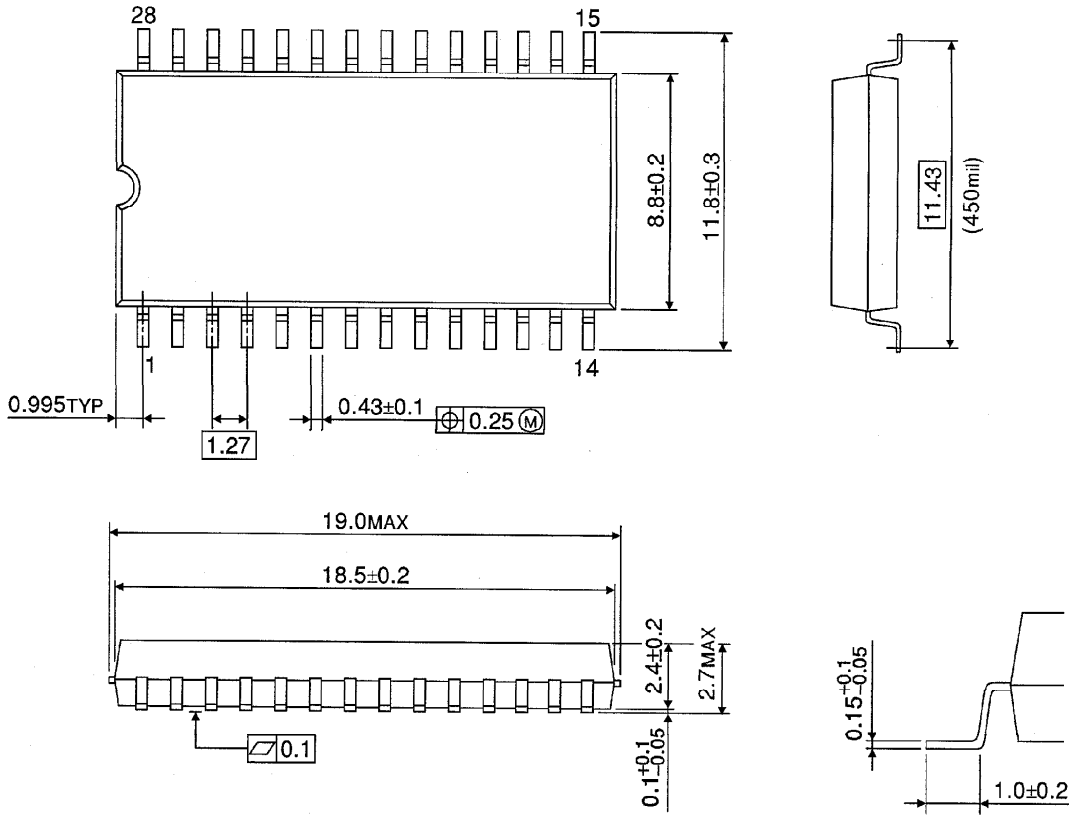
Units in mm



Weight: 4.42 g (typ)

PACKAGE DIMENSIONS (SOP28-P-450-1.27)

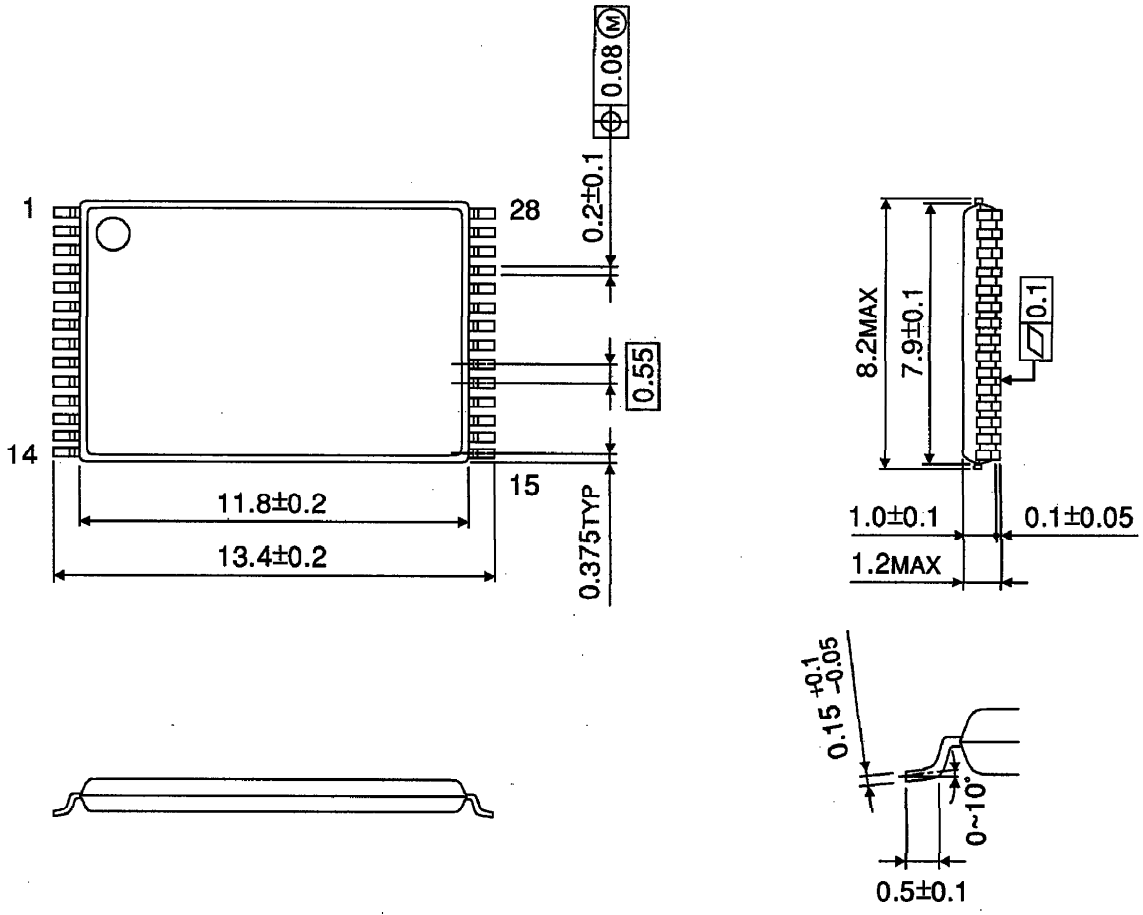
Units in mm



Weight: 0.79 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55)

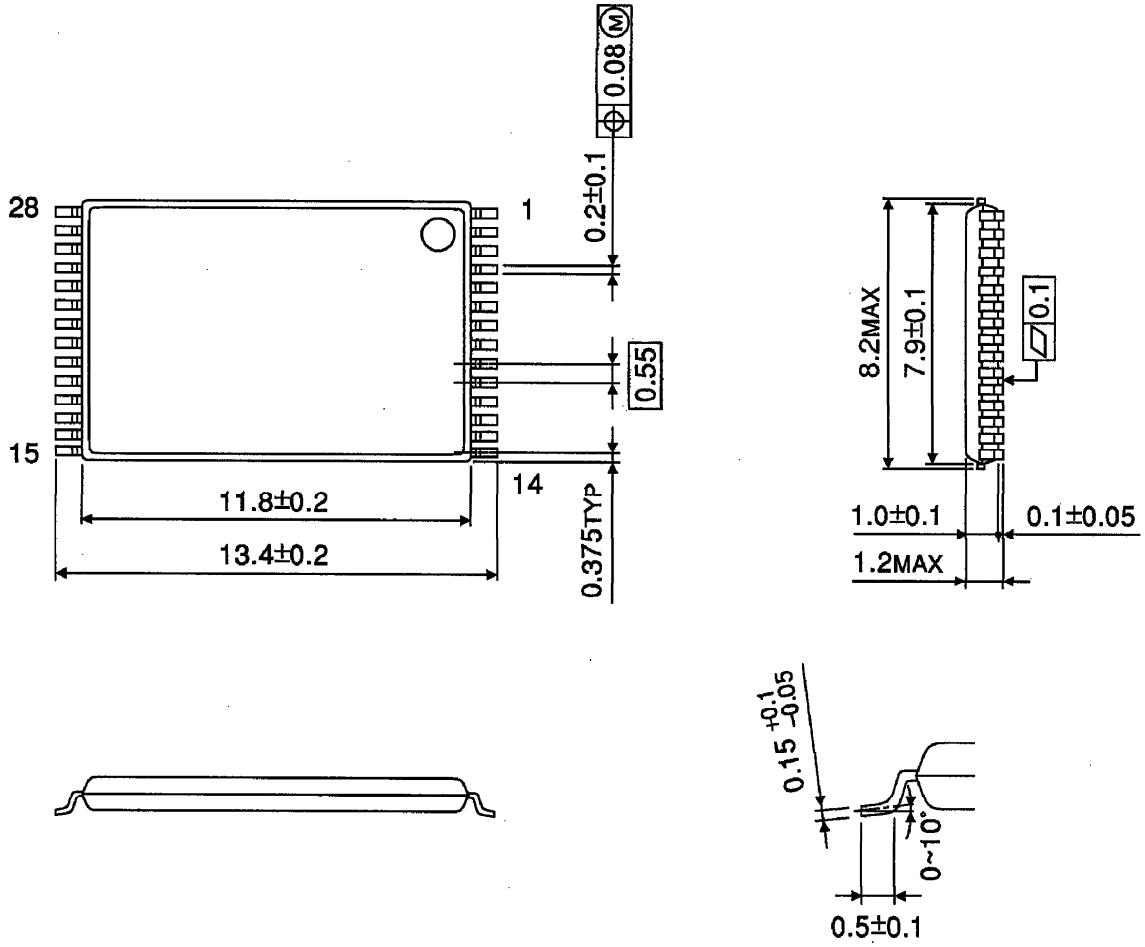
Units in mm



Weight: 0.22 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55A)

Units in mm



Weight: 0.22 g (typ)